



JCT151C-800R 12A SCR

Rev.A.1.1

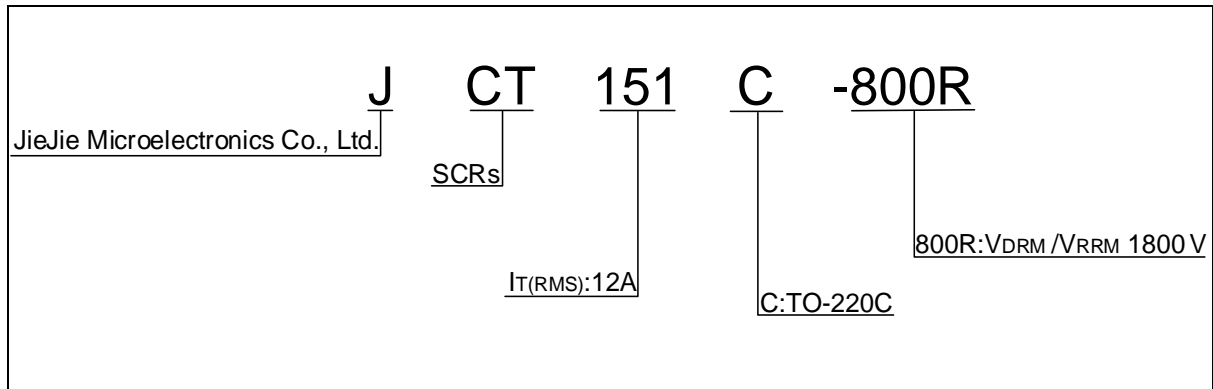
DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151C-800R of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.

It i> tc08 Tw 2.78 0 Td ( )Tj 0.004 2c -0.004 800800R-47(p)E170c(10295s)E2(T)W (04)612)24.51 Tre [(0.7

Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_{jvTJ ET Q D q e W (e)TJ ET Q q 9410$ )			

ORDERING INFORMATION



MARKING

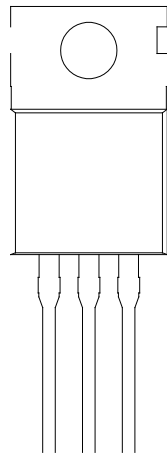


FIG.1: Maximum power dissipation versus RMS on-state current

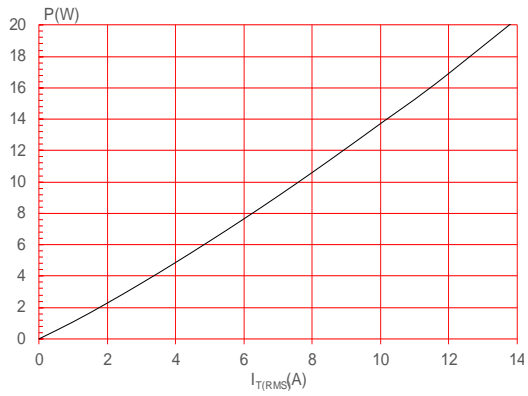


FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.







